

**Amendments to the Specification**

Please replace the title as follows:

**IMPROVEMENTS IN OR RELATING TO FILTERS METHOD FOR HERMETICALLY  
PACKAGING BULK ACOUSTIC RESONATOR DEVICE**

Please replace the paragraph beginning on page 10, lines 8-15, with the following rewritten paragraph:

The insides of the holes 39 are then coated with an insulating layer and filled with metal 40 as shown in Figure 8 using either thermal evaporation, sputtering, electroless plating, electro-plating or some combination of these or similar methods and the metal on the surface B2 is patterned to leave contact pads which can subsequently be used to make electrical contact through to the metal tracks leading to the FBAR filter. The wafer processing is then complete and the individual devices can be separated at positions indicated with lines L in Figure 8 by sawing or by etching deep grooves in the faces of the composite silicon wafer using a deep reactive ion etching process.